±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

ABSOLUTE MAXIMUM RATINGS

(All voltages referenced to GND.)	
Vcc	0.3V to +6V
I/O V _{CC}	0.3V to (V _{CC} + 0.3V)
I/O VL	0.3V to $(V_L + 0.3V)$
THREE-STATE	0.3V to $(V_L + 0.3V)$
Short-Circuit Duration I/O V _L , I/O V _{CC} t	o GNDContinuous
Short-Circuit Duration I/O VL or I/O VCO	c to GND
Driven from 40mA Source	
(except MAX3372E and MAX3377E))Continuous

Continuous Power Dissipation (T _A = +70°C)
8-Pin SOT23 (derate 8.9mW/°C above +70°C)714mW
8-Pin TDFN (derate 18.2mW/°C above +70°C)1455mW
3 x 3 UCSP (derate 4.7mW/°C above +70°C)379mW
3 x 4 UCSP (derate 6.5mW/°C above +70°C)579mW
14-Pin TSSOP (derate 9.1mW/°C above +70°C)727mW
14-Pin TDFN (derate 18.2mW/°C above +70°C)1454mW
Operating Temperature Range40°C to +85°C
Storage Temperature Range65°C to +150°C
Lead Temperature (soldering, 10s)+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{CC} = +1.65V \text{ to } +5.5V, V_L = +1.2V \text{ to } (V_{CC} + 0.3V), \text{ GND} = 0, I/O V_L \text{ and } I/O V_{CC} \text{ unconnected, } T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $V_{CC} = +3.3V$, $V_L = +1.8V$, $T_A = +25^{\circ}C$.) (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLIES						
V _L Supply Range	VL		1.2		5.5	V
V _{CC} Supply Range	V _C C		1.65		5.50	V
Supply Current from V _{CC}	IQVcc			130	300	μΑ
Supply Current from V _L	IQVL			16	100	μΑ
V _{CC} Three-State Output Mode Supply Current	ITHREE-STATE-VCC	T _A = +25°C, THREE-STATE = GND		0.03	1	μΑ
V _L Three-State Output Mode Supply Current	ITHREE-STATE-VL	T _A = +25°C, THREE-STATE = GND		0.03	1	μΑ
Three-State Output Mode Leakage Current I/O V _L _ and I/O V _{CC} _	ITHREE-STATE-LKG	T _A = +25°C, THREE-STATE = GND		0.02	1	μΑ
THREE-STATE Pin Input Leakage		T _A = +25°C		0.02	1	μΑ
ESD PROTECTION						
		IEC 1000-4-2 Air-Gap Discharge		±8		
I/O V _{CC} (Note 3)		IEC 1000-4-2 Contact Discharge		±8		kV
		Human Body Model		±15		
LOGIC-LEVEL THRESHOLDS (MAX3372E/MAX337	7E)				
I/O V _{L_} Input-Voltage High	V _{IHL}		V _L - 0.3	2		V
I/O V _{L_} Input-Voltage Low	V _{ILL}				0.15	V

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +1.65V \text{ to } +5.5V, V_L = +1.2V \text{ to } (V_{CC} + 0.3V), \text{ GND} = 0, I/O V_L \text{ and I/O } V_{CC} \text{ unconnected, } T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $V_{CC} = +3.3V, V_L = +1.8V, T_A = +25^{\circ}C.$ (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS	MIN TYP	MAX	UNITS
I/O V _{CC} _ Input-Voltage High	VIHC		V _C C - 0.4		V
I/O V _{CC} _ Input-Voltage Low	VILC			0.15	V
I/O V _{L_} Output-Voltage High	Vohl	I/O V _{L_} source current = 20µA, I/O V _{CC_} ≥ V _{CC} - 0.4V	0.67 × V _L		V
I/O V _{L_} Output-Voltage Low	V _{OLL}	I/O V _{L_} sink current = 20µA, I/O V _{CC_} ≤ 0.15V		0.4	V
I/O V _{CC} _ Output-Voltage High	V _{OHC}	I/O V_{CC} source current = 20 μ A, I/O $V_{L} \ge V_{L}$ - 0.2 V	0.67 × V _{CC}		V
I/O V _{CC} _ Output-Voltage Low	V _{OLC}	I/O V _{CC} sink current = 20μ A, I/O V _L ≤ 0.15 V		0.4	V
THREE-STATE Input-Voltage High	VIL-THREE-STATE		V _L - 0.2		V
THREE-STATE Input-Voltage Low	VIL-THREE-STATE			0.15	V
LOGIC-LEVEL THRESHOLDS (I	MAX3373E-MAX33	76E/MAX3378E/MAX3379E and MAX3	390E-MAX3393E)	
I/O V _{L_} Input-Voltage High	VIHL		V _L - 0.2		V
I/O V _L _Input-Voltage Low	V _{ILL}			0.15	V
I/O V _{CC} _ Input-Voltage High	V _{IHC}		V _{CC} - 0.4		V
I/O V _{CC} _ Input-Voltage Low	VILC			0.15	V
I/O V _{L_} Output-Voltage High	Vohl	I/O V _{L_} source current = 20µA, I/O V _{CC_} ≥ V _{CC} - 0.4V	0.67 × V _L		V
I/O V _{L_} Output-Voltage Low	V _{OLL}	I/O V _{L_} sink current = 1mA, I/O V _{CC_} ≤ 0.15V		0.4	V
I/O V _{CC} _ Output-Voltage High	VOHC	I/O V _{CC} source current = 20μ A, I/O V _L \geq V _L - 0.2 V	0.67 × V _{CC}		V
I/O V _{CC} Output-Voltage Low	V _{OLC}	I/O V _{CC} _ sink current = 1mA, I/O V _L _ ≤ 0.15V		0.4	V
THREE-STATE Input-Voltage High	VIH-THREE-STATE		V _L - 0.2		V
THREE-STATE Input-Voltage Low	VIL-THREE-STATE			0.15	V

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

TIMING CHARACTERISTICS

 $(V_{CC} = +1.65 \text{V to} +5.5 \text{V}, V_{L} = +1.2 \text{V to} (V_{CC} + 0.3 \text{V}), \text{ GND} = 0, \text{R}_{LOAD} = 1 \text{M}\Omega, \text{I/O test signal of Figure 1, T}_{A} = \text{T}_{MIN} \text{ to T}_{MAX}, \text{ unless otherwise noted. Typical values are at V}_{CC} = +3.3 \text{V}, V_{L} = +1.8 \text{V}, T}_{A} = +25 \text{°C}, \text{ unless otherwise noted.})$ (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
MAX3372E/MAX3377E (CLOAD	o = 50pF)	•					
I/O V _{CC} _ Rise Time (Note 4)	^t RVCC				1100		ns
I/O V _{CC} _ Fall Time (Note 5)	tFVCC				1000		ns
I/O V _L _ Rise Time (Note 4)	t _{RVL}				600		ns
I/O V _L Fall Time (Note 5)	t _{FVL}				1100		ns
Propagation Delay	I/O _{VL-VCC}	Driving I/O V _L _				1.6	0
Fropagation Delay	I/O _{VCC-VL}	Driving I/O V _{CC} _				1.6	μs
Channel-to-Channel Skew	tskew	Each translator equ	ally loaded			500	ns
Maximum Data Rate		C _L = 25pF		230			kbps
MAX3373E-MAX3376E/MAX337	8E/MAX3379E	and MAX3390E-MAX3	393E (C _{LOAD} = 15pF, Driv	er Output	Impeda	nce ≤ 50 Ω	2)
+1.2V ≤ V _L ≤ V _{CC} ≤ +5.5V							
I/O Vesa Dissa Time (Note 4)	t=1/20				7	25	20
I/O V _{CC} _ Rise Time (Note 4)	tRVCC	Open-drain driving		170	400	ns	
I/O)/ Fall Time (Note 5)					6	37	
I/O V _{CC} _ Fall Time (Note 5)	tFVCC	Open-drain driving		20		50	ns
I/O)/. Digo Timo (Noto 4)	t=				8	30	20
I/O V _L _ Rise Time (Note 4)	t _{RVL}	Open-drain driving			180	400	ns
I/O)/, Fall Time (Note 5)	+, =, ,				3	30	20
I/O V _{L_} Fall Time (Note 5)	tLFV	Open-drain driving			30	60	ns
	1/0.4	Driving I/O VL_			5	30	
Propagation Dalay	I/OVL-VCC		Open-drain driving		210	1000	200
Propagation Delay	1/0	Driving I/O V = =			4	30	ns
	I/Ovcc-vl	Driving I/O V _{CC} _	Open-drain driving		190	1000	
Channel to Channel Clean	*******	Each translator				20	
Channel-to-Channel Skew	tskew	equally loaded Open-drain driv				50	ns
Maximum Data Pata				8			Mbps
Maximum Data Rate		Open-drain driving	Open-drain driving				kbps

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

TIMING CHARACTERISTICS (continued)

 $(V_{CC} = +1.65V \text{ to } +5.5V, V_L = +1.2V \text{ to } (V_{CC} + 0.3V), \text{ GND} = 0, \text{ R}_{LOAD} = 1M\Omega, \text{ I/O test signal of Figure 1, T}_A = T_{MIN} \text{ to T}_{MAX}, \text{ unless otherwise noted. Typical values are at V}_{CC} = +3.3V, V_L = +1.8V, T}_A = +25^{\circ}\text{C}, \text{ unless otherwise noted.}$ (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
+1.2V ≤ V _L ≤ V _{CC} ≤ +3.3V							
I/O V _{CC} _ Rise Time (Note 4)	tRVCC				25	ns	
I/O V _{CC} _ Fall Time (Note 5)	tFVCC				30	ns	
I/O V _L _ Rise Time (Note 4)	t _{RVL}				30	ns	
I/O V _L _ Fall Time (Note 5)	t _{FVL}				30	ns	
Propagation Delay	I/O _{VL-VCC}	Driving I/O V _L			20	no	
Fropagation Delay	I/O _{VCC-VL}	Driving I/O V _{CC} _			20	ns	
Channel-to-Channel Skew	tskew	Each translator equally loaded			10	ns	
Maximum Data Rate			10			Mbps	
$\textbf{+2.5V} \leq \textbf{V}_{\textbf{L}} \leq \textbf{V}_{\textbf{CC}} \leq \textbf{+3.3V}$							
I/O V _{CC} _ Rise Time (Note 4)	tRVCC				15	ns	
I/O V _{CC} _ Fall Time (Note 5)	tFVCC				15	ns	
I/O V _L _ Rise Time (Note 4)	t _{RVL}				15	ns	
I/O V _L _ Fall Time (Note 5)	t _{FVL}				15	ns	
Propagation Delay	I/O _{VL-VCC}	Driving I/O V _L			15	no	
Fropagation Delay	I/Ovcc-vl	Driving I/O V _{CC} _			15	ns	
Channel-to-Channel Skew	tskew	Each translator equally loaded			10	ns	
Maximum Data Rate			16			Mbps	
$\textbf{+1.8V} \leq \textbf{V}_{\textbf{L}} \leq \textbf{V}_{\textbf{CC}} \leq \textbf{+2.5V}$							
I/O V _{CC} _ Rise Time (Note 4)	tRVCC				15	ns	
I/O V _{CC} _ Fall Time (Note 5)	tFVCC				15	ns	
I/O V _L _ Rise Time (Note 4)	t _{RVL}				15	ns	
I/O V _L _ Fall Time (Note 5)	t _{FVL}				15	ns	
Propagation Dolay	I/O _{VL-VCC}	Driving I/O V _L _			15		
Propagation Delay	I/O _{VCC-VL}	Driving I/O V _{CC} _			15	ns	
Channel-to-Channel Skew	tskew	Each translator equally loaded			10	ns	
Maximum Data Rate			16			Mbps	

Note 1: All units are 100% production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design and not production tested.

Note 2: For normal operation, ensure $V_L < (V_{CC} + 0.3V)$. During power-up, $V_L > (V_{CC} + 0.3V)$ will not damage the device.

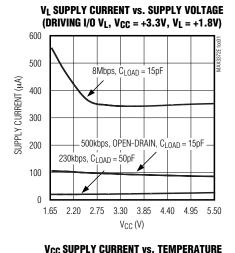
Note 3: To ensure maximum ESD protection, place a 1µF capacitor between V_{CC} and GND. See Applications Circuits.

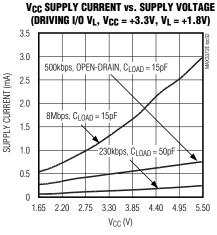
Note 4: 10% to 90% **Note 5:** 90% to 10%

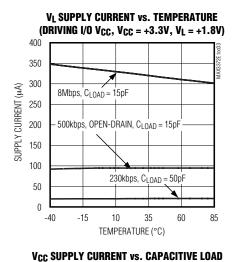
±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

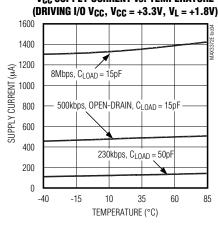
Typical Operating Characteristics

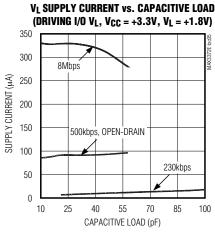
 $(R_{LOAD} = 1M\Omega, T_A = +25^{\circ}C)$, unless otherwise noted. All 230kbps TOCs apply to MAX3372E/MAX3377E only. All 8Mbps and 500kbps TOCs apply to MAX3373E–MAX3376E/MAX3378E and MAX3390E–MAX3393E only.)

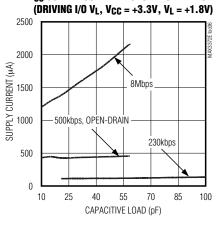


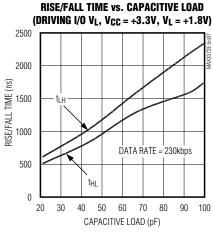


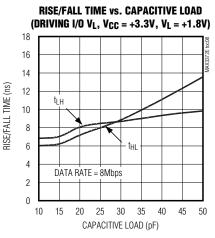


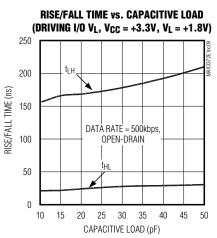








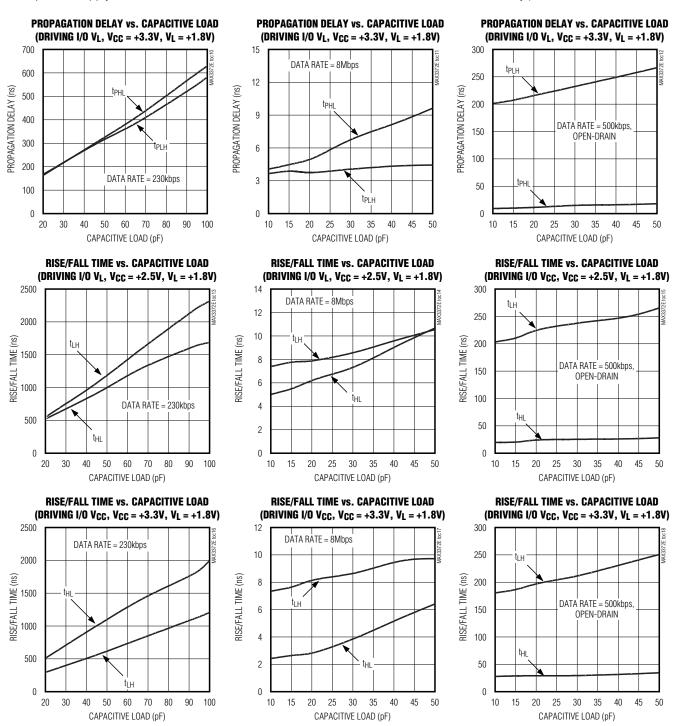




±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Typical Operating Characteristics (continued)

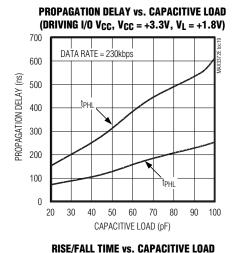
 $(R_{LOAD} = 1M\Omega, T_A = +25^{\circ}C, unless otherwise noted. All 230kbps TOCs apply to MAX3372E/MAX3377E only. All 8Mbps and 500kbps TOCs apply to MAX3373E–MAX3376E/MAX3378E and MAX3390E–MAX3393E only.)$

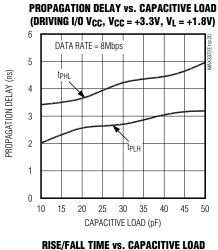


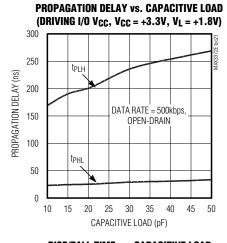
±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

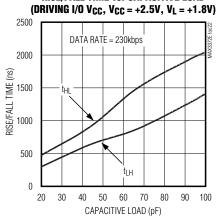
Typical Operating Characteristics (continued)

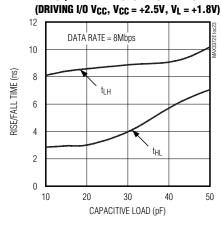
 $(R_{LOAD} = 1M\Omega, T_A = +25^{\circ}C, unless otherwise noted. All 230kbps TOCs apply to MAX3372E/MAX3377E only. All 8Mbps and 500kbps TOCs apply to MAX3373E–MAX3376E/MAX3378E/MAX3379E and MAX3390E–MAX3393E only.)$

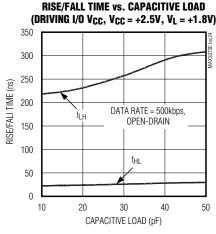


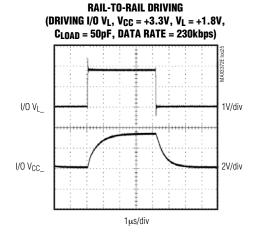


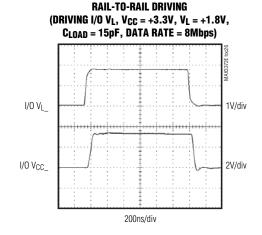








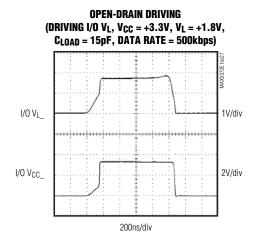


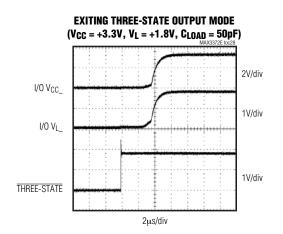


±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Typical Operating Characteristics (continued)

 $(R_{LOAD} = 1M\Omega, T_A = +25^{\circ}C, unless otherwise noted. All 230kbps TOCs apply to MAX3372E/MAX3377E only. All 8Mbps and 500kbps TOCs apply to MAX3373E–MAX3376E/MAX3378E/MAX3379E and MAX3390E–MAX3393E only.)$





Pin Description

	PIN						
3 x 4 UCSP	TSSOP	SOT23-8	3 x 3 UCSP	TDFN 8	TDFN 14	NAME	FUNCTION
A1	2	5	C2	6	1	I/O V _L 1	Input/Output 1. Referenced to V _L . (Note 6)
A2	3	4	C3	8	2	I/O VL2	Input/Output 2. Referenced to V _L . (Note 6)
АЗ	4			_	5	I/O VL3	Input/Output 3. Referenced to V _L . (Note 6)
A4	5		ĺ	_	6	I/O VL4	Input/Output 4. Referenced to V _L . (Note 6)
B1	14	7	A1	4	14	Vcc	V _{CC} Input Voltage +1.65V ≤ V _{CC} ≤ +5.5V.
B2	1	3	C1	7	10	VL	Logic Input Voltage +1.2V ≤ V _L ≤ (V _{CC} + 0.3V)
В3	8	6	B1	5	3	THREE- STATE	Three-State Output Mode Enable. Pull THREE-STATE low to place device in three-state output mode. I/O V _{CC} _ and I/O V _L _ are high impedance in three-state output mode. Note: Logic referenced to V _L (for logic thresholds see the <i>Electrical Characteristics</i> table).
B4	7	2	В3	2	7	GND	Ground
C1	13	8	A2	3	13	I/O V _{CC} 1	Input/Output 1. Referenced to V _{CC} . (Note 6)
C2	12	1	А3	1	12	I/O V _{CC} 2	Input/Output 2. Referenced to V _{CC} . (Note 6)
C3	11	_	_	_	9	I/O V _{CC} 3	Input/Output 3. Referenced to V _{CC} . (Note 6)
C4	10				8	I/O V _{CC} 4	Input/Output 4. Referenced to VCC. (Note 6)
	6, 9	_	B2	_	4, 11	N.C.	No Connection. Not internally connected.
_	_	_	_	EP	EP	EP	Exposed Pad. Connect to ground.

Note 6: For unidirectional devices (MAX3374E/MAX3375E/MAX3376E/MAX3379E and MAX3390E–MAX3393E) see the *Pin Configurations* for input/output configurations.

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Detailed Description

The MAX3372E-MAX3379E and MAX3390E-MAX3393E ESD-protected level translators provide the level shifting necessary to allow data transfer in a multivoltage system. Externally applied voltages, VCC and VL, set the logic levels on either side of the device. A low-voltage logic signal present on the V_I side of the device appears as a highvoltage logic signal on the Vcc side of the device, and vice-versa. The MAX3374E/MAX3375E/MAX3376E/ MAX3379E and MAX3390E-MAX3393E unidirectional level translators level shift data in one direction (V_L → VCC or VCC → VL) on any single data line. The MAX3372E/MAX3373E and MAX3377E/MAX3378E bidirectional level translators utilize a transmission-gatebased design (see Figure 2) to allow data translation in either direction (V_L ↔ V_{CC}) on any single data line. The MAX3372E-MAX3379E and MAX3390E-MAX3393E

accept V_L from +1.2V to +5.5V and V_{CC} from +1.65V to +5.5V, making them ideal for data transfer between low-voltage ASICs/PLDs and higher voltage systems.

All devices in the MAX3372E–MAX3379E, MAX3390E–MAX3393E family feature a three-state output mode that reduces supply current to less than 1µA, thermal short-circuit protection, and ±15kV ESD protection on the VCC side for greater protection in applications that route signals externally. The MAX3372E/MAX3377E operate at a guaranteed data rate of 230kbps. Slew-rate limiting reduces EMI emissions in all 230kbps devices. The MAX3373E–MAX3376E/MAX3378E/MAX3379E and MAX3390E–MAX3393E operate at a guaranteed data rate of 8Mbps over the entire specified operating voltage range. Within specific voltage domains, higher data rates are possible. (See the *Timing Characteristics* table.)

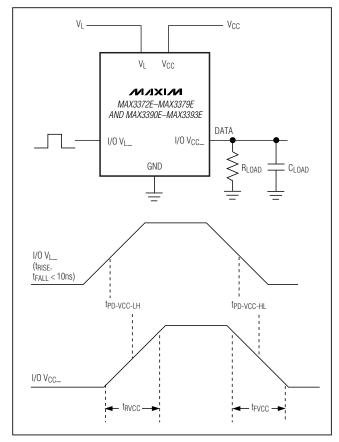


Figure 1a. Rail-to-Rail Driving I/O VL

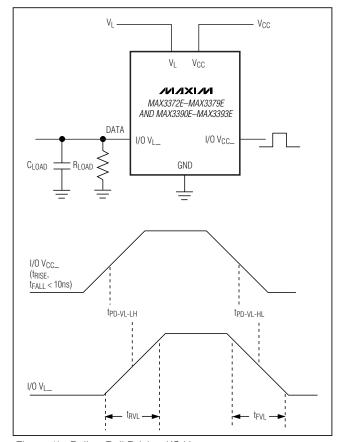


Figure 1b. Rail-to-Rail Driving I/O VCC

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Level Translation

For proper operation ensure that $+1.65V \le V_{CC} \le +5.5V$, $+1.2V \le V_{L} \le +5.5V$, and $V_{L} \le (V_{CC} + 0.3V)$. During power-up sequencing, $V_{L} \ge (V_{CC} + 0.3V)$ will not damage the device. During power-supply sequencing, when V_{CC} is floating and V_{L} is powering up, a current may be sourced, yet the device will not latch up. The speed-up circuitry limits the maximum data rate for devices in the MAX3372E-MAX3379E, MAX3390E-MAX3393E family to 16Mbps. The maximum data rate also depends heavily on the load capacitance (see the *Typical Operating Characteristics*), output impedance of the driver, and the operational voltage range (see the *Timing Characteristics* table).

Speed-Up Circuitry

The MAX3373E–MAX3376E/MAX3378E/MAX3379E and MAX3390E–MAX3393E feature a one-shot generator that decreases the rise time of the output. When triggered, MOSFETs PU1 and PU2 turn on for a short time to pull up

I/O V_L and I/O V_{CC} to their respective supplies (see Figure 2b). This greatly reduces the rise time and propagation delay for the low-to-high transition. The scope photo of Rail-to-Rail Driving for 8Mbps Operation in the *Typical Operating Characteristics* shows the speed-up circuitry in operation.

Rise-Time Accelerators

The MAX3373E–MAX3376E/MAX3378E/MAX3379E and the MAX3390E–MAX3393E have internal rise-time accelerators allowing operation up to 16Mbps. The rise-time accelerators are present on both sides of the device and act to speed up the rise time of the input and output of the device, regardless of the direction of the data. The triggering mechanism for these accelerators is both level and edge sensitive. To prevent false triggering of the rise-time accelerators, signal fall times of less than 20ns/V are recommended for both the inputs and outputs of the device. Under less noisy conditions, longer signal fall times may be acceptable.

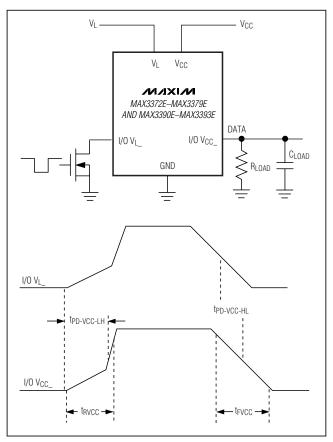


Figure 1c. Open-Drain Driving I/O VCC

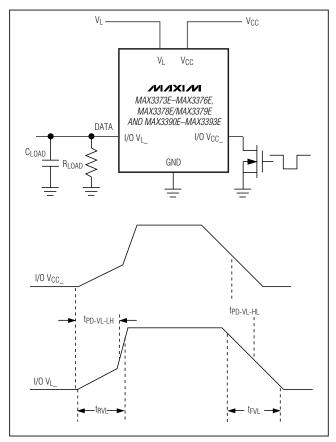


Figure 1d. Open-Drain Driving I/O VL

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Three-State Output Mode

Pull THREE-STATE low to place the MAX3372E–MAX3379E and MAX3390E–MAX3393E in three-state output mode. Connect THREE-STATE to V_L (logic-high) for normal operation. Activating the three-state output mode disconnects the internal $10k\Omega$ pullup resistors on the I/O V_C and I/O V_L lines. This forces the I/O lines to a high-impedance state, and decreases the supply current to less than $1\mu A$. The high-impedance I/O lines in three-state output mode allow for use in a multidrop network. When in three-state output mode, do not allow the voltage

at I/O V_L to exceed (V_L + 0.3V), or the voltage at I/O V_{CC} to exceed (V_{CC} + 0.3V).

Thermal Short-Circuit Protection

Thermal overload detection protects the MAX3372E–MAX3379E and MAX3390E–MAX3393E from short-circuit fault conditions. In the event of a short-circuit fault, when the junction temperature (T_J) reaches +152°C, a thermal sensor signals the three-state output mode logic to force the device into three-state output mode. When T_J has cooled to +142°C, normal operation resumes.

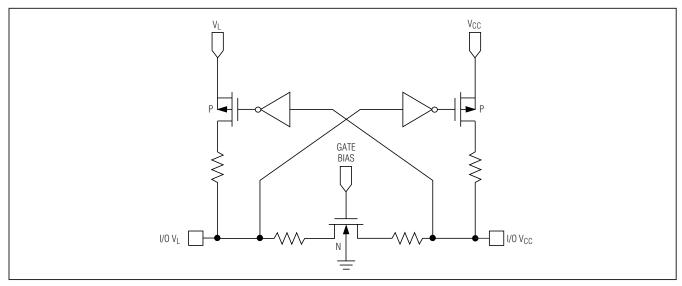


Figure 2a. Functional Diagram, MAX3372E/MAX3377E (1 I/O line)

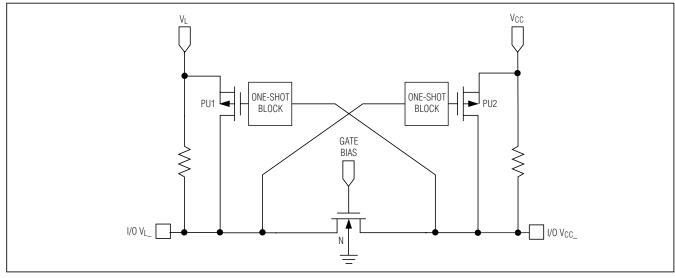


Figure 2b. Functional Diagram, MAX3373E/MAX3378E (1 I/O line)

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

±15kV ESD Protection

As with all Maxim devices, ESD-protection structures are incorporated on all pins to protect against electrostatic discharges encountered during handling and assembly. The I/O VCC lines have extra protection against static electricity. Maxim's engineers have developed state-of-the-art structures to protect these pins against ESD of ±15kV without damage. The ESD structures withstand high ESD in all states: normal operation, three-state output mode, and powered down. After an ESD event, Maxim's E versions keep working without latchup, whereas competing products can latch and must be powered down to remove latchup.

ESD protection can be tested in various ways. The I/O VCC lines of this product family are characterized for protection to the following limits:

- 1) ±15kV using the Human Body Model
- 2) ±8kV using the Contact Discharge method specified in IEC 1000-4-2
- 3) ±10kV using IEC 1000-4-2's Air-Gap Discharge method

ESD Test Conditions

ESD performance depends on a variety of conditions. Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

Human Body Model

Figure 3a shows the Human Body Model and Figure 3b shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the test device through a $1.5 \mathrm{k}\Omega$ resistor.

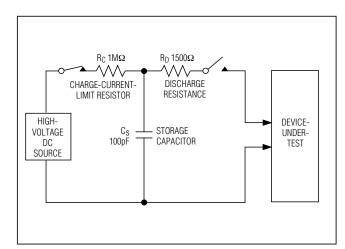


Figure 3a. Human Body ESD Test Model

IEC 1000-4-2

The IEC 1000-4-2 standard covers ESD testing and performance of finished equipment; it does not specifically refer to integrated circuits. The MAX3372E–MAX3379E and MAX3390E–MAX3393E help to design equipment that meets Level 3 of IEC 1000-4-2, without the need for additional ESD-protection components.

The major difference between tests done using the Human Body Model and IEC 1000-4-2 is higher peak current in IEC 1000-4-2, because series resistance is lower in the IEC 1000-4-2 model. Hence, the ESD withstand voltage measured to IEC 1000-4-2 is generally lower than that measured using the Human Body Model. Figure 4a shows the IEC 1000-4-2 model, and Figure 4b shows the current waveform for the ±8kV, IEC 1000-4-2, Level 4, ESD contact-discharge test.

The air-gap test involves approaching the device with a charged probe. The contact-discharge method connects the probe to the device before the probe is energized.

Machine Model

The Machine Model for ESD tests all pins using a 200pF storage capacitor and zero discharge resistance. Its objective is to emulate the stress caused by contact that occurs with handling and assembly during manufacturing. Of course, all pins require this protection during manufacturing, not just inputs and outputs. Therefore, after PCB assembly, the Machine Model is less relevant to I/O ports.

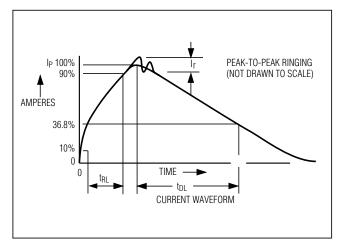


Figure 3b. Human Body Current Waveform

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

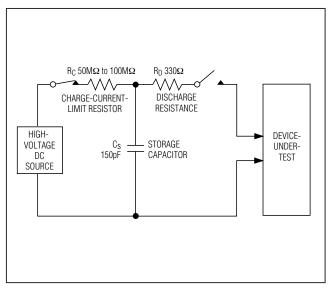


Figure 4a. IEC 1000-4-2 ESD Test Model

100% 90% t_r = 0.7ns to 1ns t

Figure 4b. IEC 1000-4-2 ESD Generator Current Waveform

Applications Information

Power-Supply Decoupling

To reduce ripple and the chance of transmitting incorrect data, bypass V_L and V_{CC} to ground with a 0.1µF capacitor. See the *Typical Operating Circuit*. To ensure full ±15kV ESD protection, bypass V_{CC} to ground with a 1µF capacitor. Place all capacitors as close to the power-supply inputs as possible.

I²C Level Translation

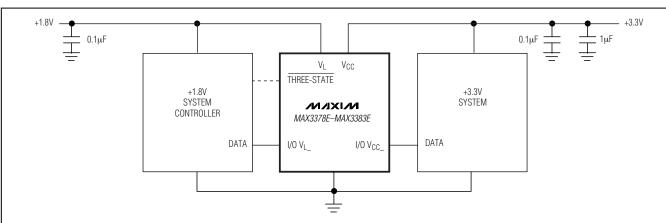
The MAX3373E-MAX3376E, MAX3378E/MAX3379E and MAX3390E-MAX3393E level-shift the data present on the I/O lines between +1.2V and +5.5V, making them ideal for level translation between a low-voltage

ASIC and an I²C device. A typical application involves interfacing a low-voltage microprocessor to a 3V or 5V D/A converter, such as the MAX517.

Push-Pull vs. Open-Drain Driving

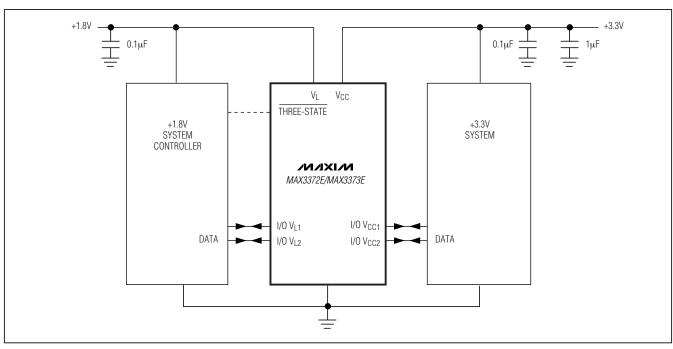
All devices in the MAX3372E–MAX3379E and MAX3390E–MAX3393E family may be driven in a push-pull configuration. The MAX3373E–MAX3376E/MAX3378E/MAX3379E and MAX3390E–MAX3393E include internal $10k\Omega$ resistors that pull up I/O V_L and I/O V_{CC} to their respective power supplies, allowing operation of the I/O lines with open-drain devices. See the *Timing Characteristics* table for maximum data rates when using open-drain drivers.

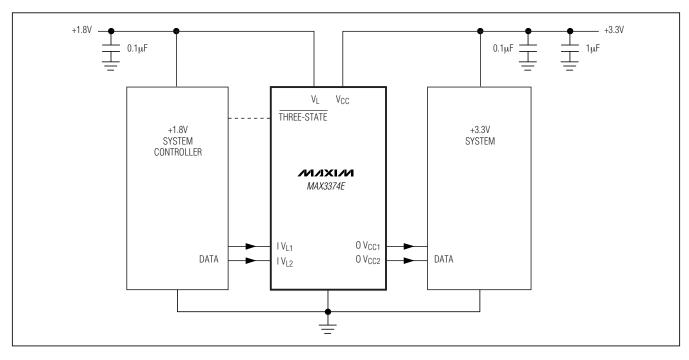
Typical Operating Circuit



±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

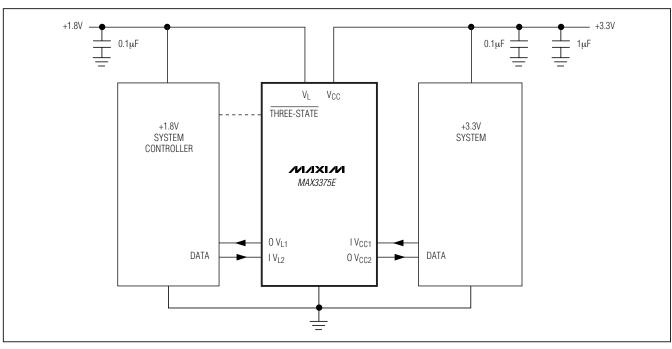
Applications Circuits

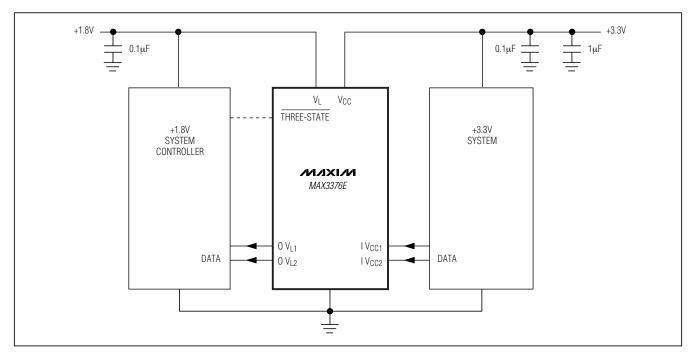




±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

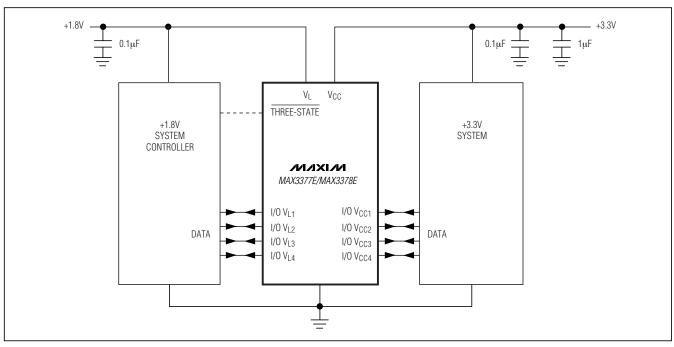
Applications Circuits (continued)

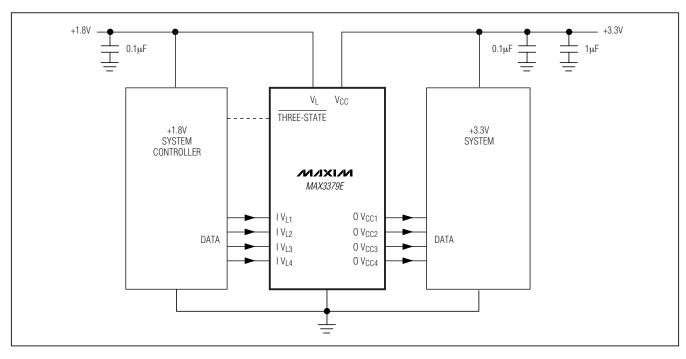




±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

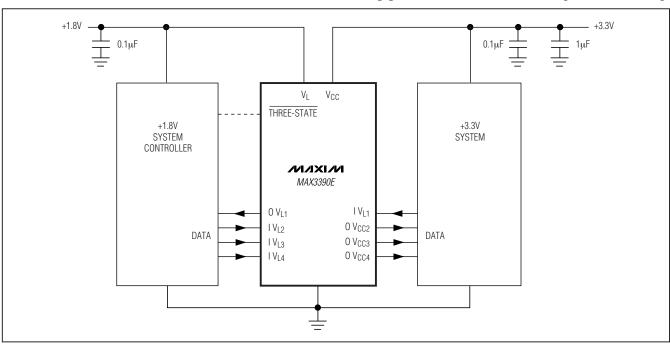
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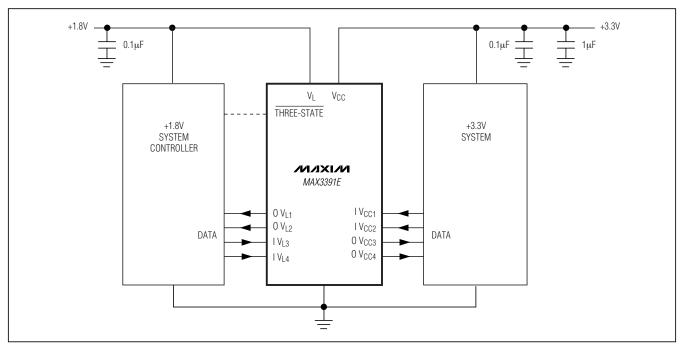




±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

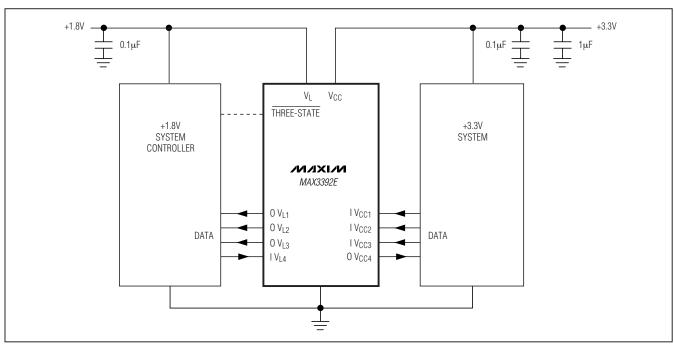
Applications Circuits (continued)

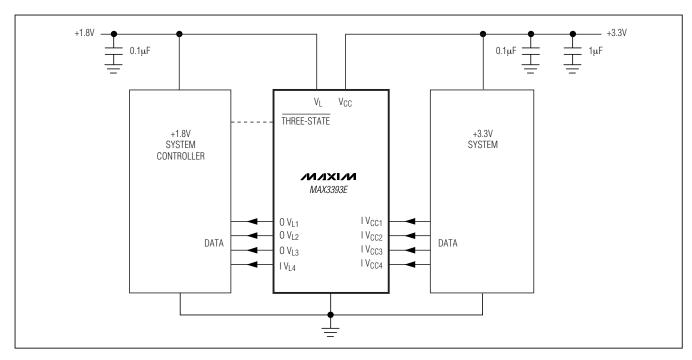




±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Applications Circuits (continued)





±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Selector Guide

LEVEL T / DATA							
PART	TRANS- LATION	Tx/ Rx [†]	DATA RATE	TOP MARK			
MAX3372EEKA+T	√ Bi	2/2		AAKO			
MAX3372EEBL+T	√ Bi	2/2	230kbps	AAR			
MAX3372EETA+T	√ Bi	2/2		AQG			
MAX3373EEKA+T	√ Bi	2/2		AAKS			
MAX3373EEBL+T	√ Bi	2/2		AAZ			
MAX3373EETA+T	√ Bi	2/2		AQH			
MAX3374EEKA+T	Uni	2/0		AALH			
MAX3374EEBL+T	Uni	2/0		ABA			
MAX3374EETA+T	Uni	2/0	OMboo*	AQI			
MAX3375EEKA+T	Uni	1/1	8Mbps*	AALI			
MAX3375EEBL+T	Uni	1/1		ABB			
MAX3375EETA+T	Uni	1/1		AQJ			
MAX3376EEKA+T	Uni	0/2		AALG			
MAX3376EEBL+T	Uni	0/2		AAV			
MAX3376EETA+T	Uni	0/2		AQK			
MAX3377EEUD	√ Bi	4/4		_			
MAX3377EEBC+T	√ Bi	4/4	230kbps	AAX			
MAX3377EETD+T	√ Bi	4/4		AAG			
MAX3378EEUD	√ Bi	4/4		_			
MAX3378EEBC+T	√ Bi	4/4		AAY			
MAX3378EETD+T	√ Bi	4/4		AAH			
MAX3379EEUD	Uni	4/0		_			
MAX3379EEBC+T	Uni	4/0		AAZ			
MAX3379EETD+T	Uni	4/0		AAI			
MAX3390EEUD	Uni	3/1		_			
MAX3390EEBC+T	Uni	3/1		ABA			
MAX3390EETD+T	Uni	3/1	OMboo*	AAJ			
MAX3391EEUD	Uni	2/2	8Mbps*	_			
MAX3391EEBC+T	Uni	2/2		ABB			
MAX3391EETD+T	Uni	2/2		AAK			
MAX3392EEUD	Uni	1/3					
MAX3392EEBC+T	Uni	1/3		ABC			
MAX3392EETD+T	Uni	1/3		AAL			
MAX3393EEUD	Uni	0/4					
MAX3393EEBC+T	Uni	0/4		ABD			
MAX3393EETD+T	Uni	0/4		AAM			

 $^{^{\}dagger}Tx = V_L \rightarrow V_{CC}, Rx = V_{CC} \rightarrow V_L$

__Ordering Information (continued)

PART	TEMP RANGE	PIN- PACKAGE	PKG CODE
MAX3372EEBL+T	-40°C to +85°C	9 UCSP (1.5mm x 1.5mm)	B9-2
MAX3372EETA+T	-40°C to +85°C	8 TDFN-EP** (3mm x 3mm)	T833-2
MAX3373EEKA+T	-40°C to +85°C	8 SOT23	K8S-3
MAX3373EEBL+T	-40°C to +85°C	9 UCSP (1.5mm x 1.5mm)	B9-2
MAX3373EETA+T	-40°C to +85°C	8 TDFN-EP** (3mm x 3mm)	T833-2
MAX3374EEKA+T	-40°C to +85°C	8 SOT23	K8S-3
MAX3374EEBL+T	-40°C to +85°C	9 UCSP (1.5mm x 1.5mm)	B9-2
MAX3374EETA+T	-40°C to +85°C	8 TDFN-EP** (3mm x 3mm)	T833-2
MAX3375EEKA+T	-40°C to +85°C	8 SOT23	K8S-3
MAX3375EEBL+T	-40°C to +85°C	9 UCSP (1.5mm x 1.5mm)	B9-2
MAX3375EETA+T	-40°C to +85°C	8 TDFN-EP** (3mm x 3mm)	T833-2
MAX3376EEKA+T	-40°C to +85°C	8 SOT23	K8S-3
MAX3376EEBL+T	-40°C to +85°C	9 UCSP (1.5mm x 1.5mm)	B9-2
MAX3376EETA+T	-40°C to +85°C	8 TDFN-EP** (3mm x 3mm)	T833-2
MAX3377EEUD	-40°C to +85°C	14 TSSOP	U14-1
MAX3377EEBC+T	-40°C to +85°C	9 UCSP (1.5mm x 1.5mm)	B12-1
MAX3377EETD+T	-40°C to +85°C	14 TDFN-EP** (3mm x 3mm)	T1433-2
MAX3378EEUD	-40°C to +85°C	14 TSSOP	U14-1
MAX3378EEBC+T	-40°C to +85°C	12 UCSP (1.5mm x 2.0mm)	B12-1
MAX3378EETD+T	-40°C to +85°C	14 TDFN-EP** (3mm x 3mm)	T1433-2

⁺Denotes a lead-free package.

^{*}Higher data rates are possible (see the Timing Characteristics table).

^{**}EP = Exposed pad.

T = Tape and reel.

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Ordering Information (continued)

PART	TEMP RANGE	PIN- PACKAGE	PKG CODE
MAX3379EEUD [†]	-40°C to +85°C	14 TSSOP	U14-1
MAX3379EEBC+T [†]	-40°C to +85°C	12 UCSP (1.5mm x 2.0mm)	B12-1
MAX3379EETD+T [†]	-40°C to +85°C	14 TDFN-EP** (3mm x 3mm)	T1433-2
MAX3390EEUD [†]	-40°C to +85°C	14 TSSOP	U14-1
MAX3390EEBC+T [†]	-40°C to +85°C	12 UCSP (1.5mm x 2.0mm)	B12-1
MAX3390EETD+T	-40°C to +85°C	14 TDFN-EP** (3mm x 3mm)	T1433-2
MAX3391EEUD [†]	-40°C to +85°C	14 TSSOP	U14-1
MAX3391EEBC+T [†]	-40°C to +85°C	12 UCSP (1.5mm x 2.0mm)	B12-1
MAX3391EETD+T	-40°C to +85°C	14 TDFN-EP** (3mm x 3mm)	T1433-2
MAX3392EEUD [†]	-40°C to +85°C	14 TSSOP	U14-1
MAX3392EEBC+T [†]	-40°C to +85°C	12 UCSP (1.5mm x 2.0mm)	B12-1
MAX3392EETD+T	-40°C to +85°C	14 TDFN-EP** (3mm x 3mm)	T1433-2
MAX3393EEUD [†]	-40°C to +85°C	14 TSSOP	U14-1
MAX3393EEBC+T [†]	-40°C to +85°C	12 UCSP (1.5mm x 2.0mm)	B12-1
MAX3393EETD+T [†]	-40°C to +85°C	14 TDFN-EP** (3mm x 3mm)	T1433-2

⁺Denotes a lead-free package.

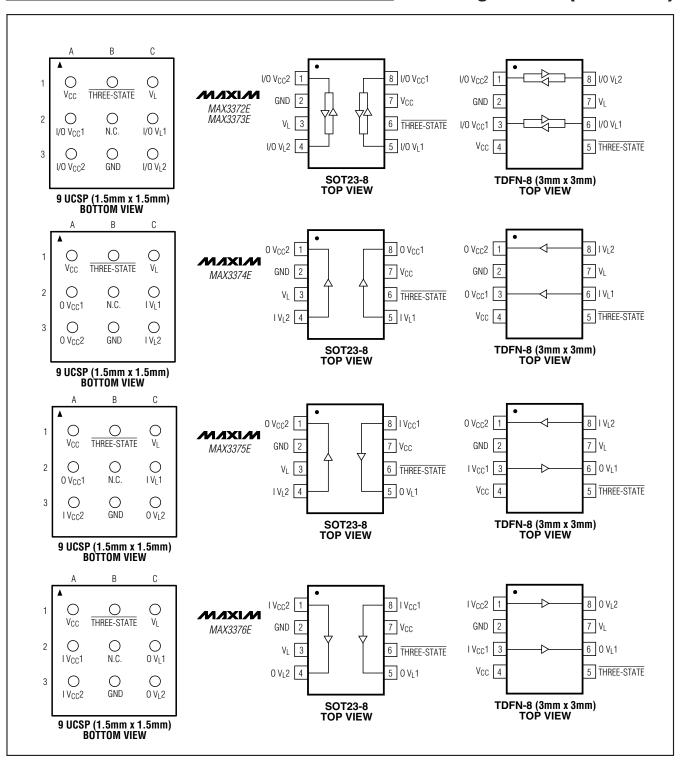
^{**}EP = Exposed pad.

T = Tape and reel.

[†]Future product—contact factory for availability.

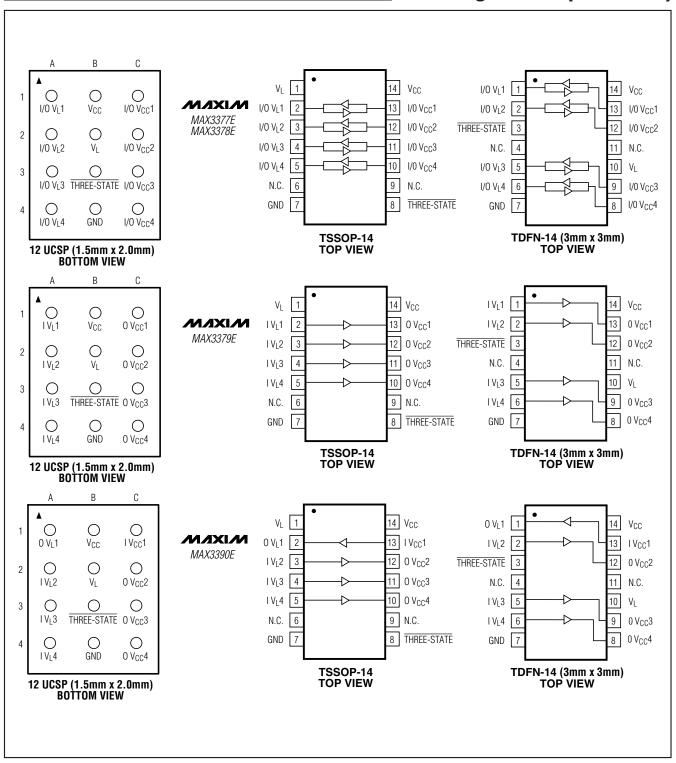
±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Pin Configurations (continued)



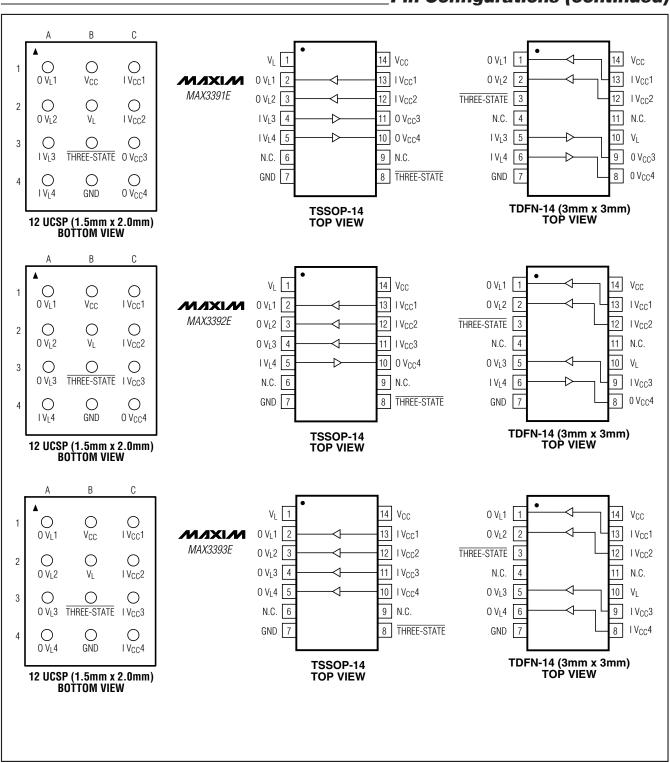
±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Pin Configurations (continued)



±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

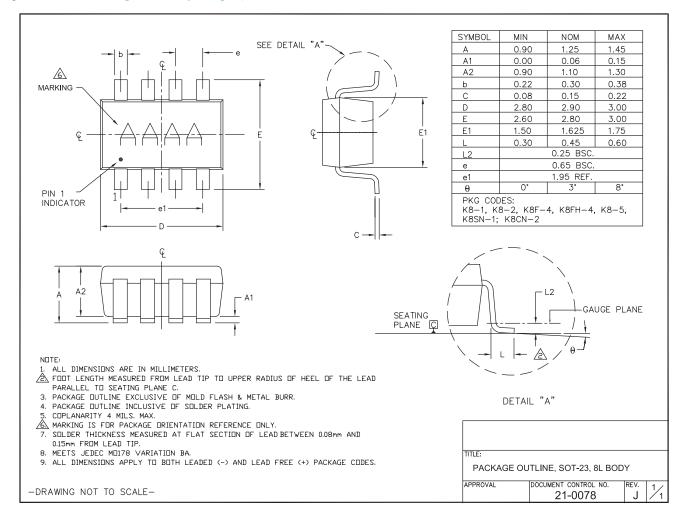
Pin Configurations (continued)



±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maximintegrated.com/packages.)



Chip Information

TRANSISTOR COUNT: MAX3372E-MAX3376E: 189

MAX3377E-MAX3379E,

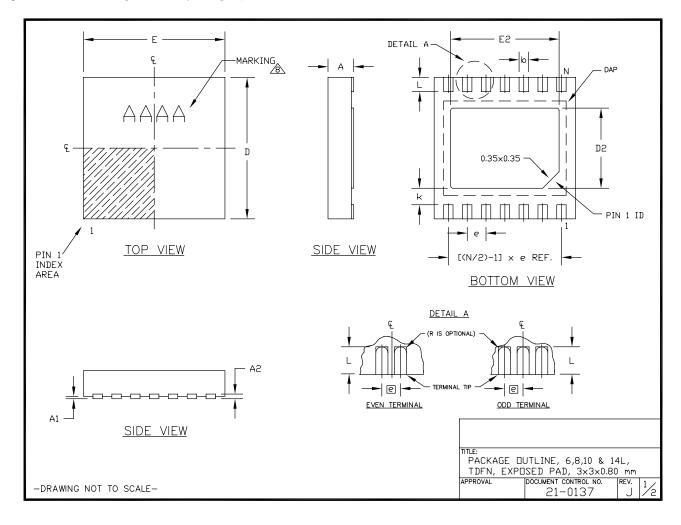
MAX3390E-MAX3393E: 295

PROCESS: BICMOS

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maximintegrated.com/packages.)



±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maximintegrated.com/packages.)

COMMON DIMENSIONS						
SYMBOL	MIN.	MAX.				
Α	0.70	0.80				
D	2.90	3.10				
E	290	3.10				
A1	0.00	0.05				
L	0.20	0.40				
k	0.25 MIN.					
A2	0.20 R ff .					

DAGKA OF M	^D IA T	1010						
P AC KAGE VAR ATIONS								
PKG.CODE	N	D2	E2	е	JEDEC SPE C	b	[(N/2)-1] x e	
T633-2	6	1.50±0.10	2.30±0.10	0.95 B SC	MO229 / WEEA	0.40±0.05	1.90 R ⊞	
T833-2	8	1.50±0.10	2.30±0.10	0.65 B SC	MO229/WEEC	0.30±0.05	1.95 R ⊞	
T833-3	8	1.50±0.10	2.30±0.10	0.65 B SC	MO229/WEEC	0.30±0.05	1.95 R ⊞	
T1033-1	10	1.50±0.10	2.30±0.10	0.50 B SC	MO229 / WE E D3	0.25±0.05	2.00 R ⊞	
T1033MK-1	10	1.50±0.10	2.30±0.10	0.50 B SC	MO229 / WE E D3	0.25±0.05	2.00 R ⊞	
T1033-2	10	1.50±0.10	2.30±0.10	0.50 B SC	MO229 / WE E D3	0.25±0.05	2.00 R ⊞	
T1433-1	14	1.70±0.10	2.30±0.10	0.40 B SC		0.20±0.05	2.40 R ⊞	
T1433-2	14	1.70±0.10	2.30±0.10	0.40 B SC		0.20±0.05	2.40 R ⊞	
T1433-3F	14	1.70±0.10	2.30±0.10	0.40 B SC		0.20±0.05	2.40 R ⊞	

NOTES:

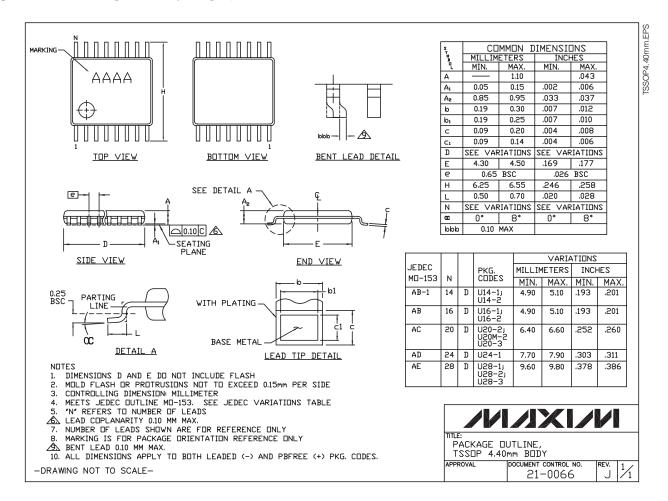
- 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
- 2. COPLANARITY SHALL NOT EXCEED 0.08 mm.
- 3. WARPAGE SHALL NOT EXCEED 0.10 mm.
- 4. PACKAGE LENGTH/PACKAGE WIDTH ARE CONSIDERED AS SPECIAL CHARACTERISTIC(S).
- 5. DRAWING CONFORMS TO JEDEC MO229, EXCEPT DIMENSIONS "D2" AND "E2", AND T1433-1 & T1433-2.
- 6. "N" IS THE TOTAL NUMBER OF LEADS.
- 7. NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.
- MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY.
- 9. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND PEFREE (+) PKG. CODES.

-DRAWING NOT TO SCALE-

±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Package Information (continued)

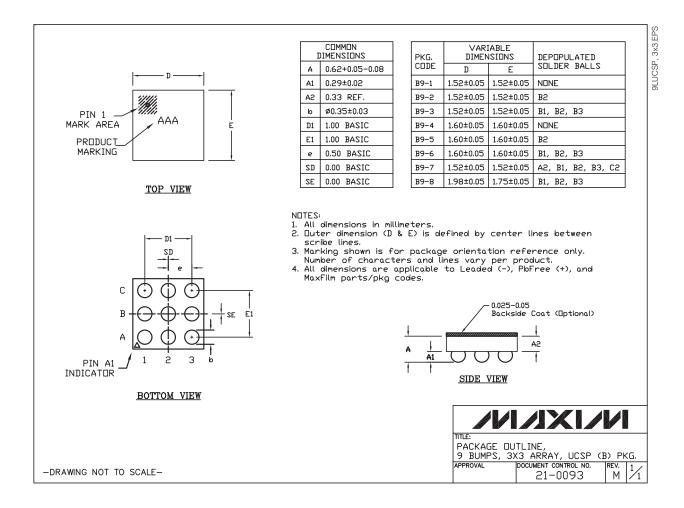
(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maximintegrated.com/packages.)



±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Package Information (continued)

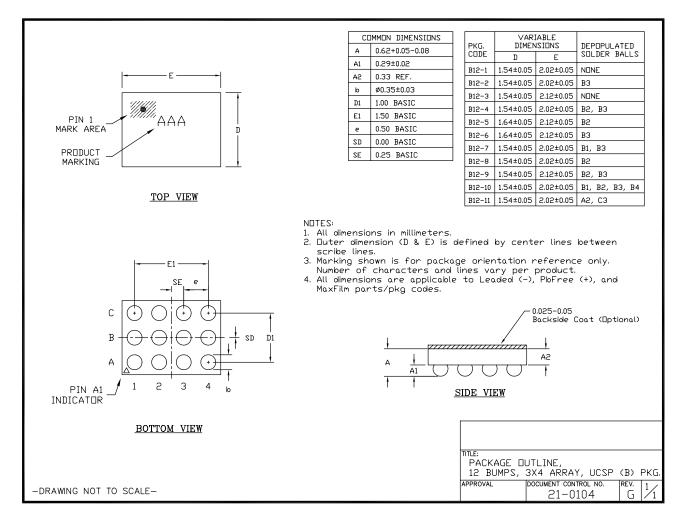
(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maximintegrated.com/packages.)



±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translators in UCSP

Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maximintegrated.com/packages.)



±15kV ESD-Protected, 1µA, 16Mbps, Dual/Quad Low-Voltage Level Translat0ors in UCSP

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	1/02	Initial Release	_
1	12/06	Addition of 12-bump ECSP packaging	-
2	11/07	Addition of lead-free options	1, 20–31



Maxim Integrated cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim Integrated product. No circuit patent licenses are implied. Maxim Integrated reserves the right to change the circuitry and specifications without notice at any time. The parametric values (min and max limits) shown in the Electrical Characteristics table are guaranteed. Other parametric values quoted in this data sheet are provided for guidance.

Maxim Integrated 160 Rio Robles, San Jose, CA 95134 USA 1-408-601-1000

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